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| Objective |
| Batch name:  |
| This is an example process flow to be used as a template. It should contain* The objective of the process
* Substrates/samples used in the flow. Both actual samples to be processed (device wafers) and monitor samples for the different process steps
* The Process flow main processes and steps
* Recommended: Figures illustrating the sample before and after each main process step.

How to use this template:* Fill out the fields in the heading!
* Add process steps by using Quick Parts under Insert (your cursor should be located below the “Comments:”-line of the previous step). Select the “Process Flow” item.
* Also other document parts can be inserted the same way: Substrate Info, Figure Table and TOC.
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| Substrates |
| Substrate | Orient. | Size | Doping/type | Polish | thickness | Box | Purpose | # | Sample ID |
| Silicon  | <100> | 4” | n (Phos.) | DSP | 350±30µm |  | Device wafers |  |  |
| Silicon  | <100> | 4” | n (Phos.) | DSP | 350±30µm |  | Dummy wafer |  |  |

Comments: wafer bow on S1-S10 should be <2µm

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| 1. Preparation
 |
| Step Heading | Equipment | Procedure | Recipe/mask | Target±tol. | Comments |
| * 1. Wafer selection
 | Wafer box | Take the wafers from the storage and put them in a wafer box. Take the monitors from the box and put them in a sample tray. |  |  | Note the wafer IDs in the batch traveler |
| * 1. Cleaning
 | 7-Up | Clean all wafers and monitors |  |  |  |
| * 1. Inspection
 | lamp | Optical inspect wafers |  |  | Take new wafers if they cannot be well cleaned |
| * 1. Start bake-out
 | 250°C oven | Place steel carrier with the wafers and monitors in the oven | Bake250 | >1 hour | 1 hour baking |

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| 1. Lithography
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| Step Heading | Equipment | Procedure | Recipe/mask | Target±tol. | Comments |
| * 1. Surface treatment
 | HMDS oven | Load all wafers in oven for xx mins | Recipe 4 | >xx mins | Note time in traveler |
| * 1. Clean spinner
 | Track 1 | Clean spinner nozzle and run the dummy wafer |  |  |  |
| * 1. Coat wafers
 | Track 1 | Coat the sharp wafersAZ5214e Novolac resistSoftbake on hotplate, 90°C, 60 sec | Recipe: PR1\_5 | 1.5µm±0.2µm | Resist thickness not checked |
| * 1. Exposure
 | KS aligner | Align to flat. Expose for xx sec | Mask: lines1 |  |  |
| * 1. Develop
 | Wet bench | Develop in YYYY for 120 sec |  | 120±10s | Note time in traveler |
| * 1. Rinse
 | Wet bench | Rinse in DI water for 5 min |  | 300±30s |  |

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| Figures |
| Figure Caption | Figure | Step reference |
| 1. After development
 |  | 2 Lithography |

Comments:Click here to enter text.

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